# **General Purpose Transistors**

# **PNP Silicon**

#### **Features**

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-60	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current - Continuous	Ic	-600	mAdc
Collector Current - Peak (Note 3)	I <sub>CM</sub>	-1200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

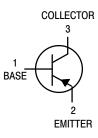
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236AB) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



2F = Device Code M = Date Code\* • = Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

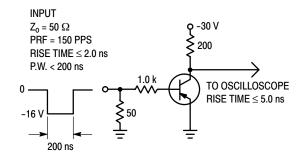
Device	Package	Shipping <sup>†</sup>
MMBT2907ALT1G	SOT-23	3000 / Tape &
SMMBT2907ALT1G	(Pb-Free)	Reel
MMBT2907ALT3G	SOT-23	10,000 / Tape &
SMMBT2907ALT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					•
Collector-Emitter Breakdown Voltage (Not $(I_C = -1.0 \text{ mAdc}, I_B = 0)$ $(I_C = -10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	-60 -60		Vdc	
Collector - Base Breakdown Voltage (I <sub>C</sub> =	-10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-60	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -	10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = -30 Vdc,	$V_{EB(off)} = -0.5 \text{ Vdc}$	I <sub>CEX</sub>	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	I <sub>CBO</sub>	- -	-0.010 -10	μAdc	
Base Cutoff Current (V <sub>CE</sub> = −30 Vdc, V <sub>EE</sub>	<sub>(off)</sub> = -0.5 Vdc)	I <sub>BL</sub>	-	-50	nAdc
ON CHARACTERISTICS					
$\begin{array}{c} \text{DC Current Gain} \\ (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \end{array}$	e 4)	h <sub>FE</sub>	75 100 100 100 50	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (Note 4) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)		V <sub>CE(sat)</sub>	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 4 $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	V <sub>BE(sat)</sub>	- -	-1.3 -2.6	Vdc	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Notes 4, 5), (I <sub>C</sub> = –50 mAdc, V <sub>CE</sub> = –20 Vdc, f = 100 MHz)		f <sub>T</sub>	200	-	MHz
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	8.0	pF
Input Capacitance (V <sub>EB</sub> = -2.0 Vdc, I <sub>C</sub> =	0, f = 1.0 MHz)	C <sub>ibo</sub>	-	30	
SWITCHING CHARACTERISTICS			,		-
Turn-On Time		t <sub>on</sub>	_	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B_1} = -15 \text{ mAdc})$	t <sub>d</sub>	-	10	
Rise Time	,	t <sub>r</sub>	-	40	]
Turn-Off Time		t <sub>off</sub>	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$		_	80	
IB1 = IB2 = =13 IIIA00)		t <sub>f</sub>	-	30	

- 4. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- 5.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.





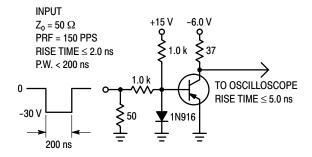


Figure 2. Storage and Fall Time Test Circuit

#### **TYPICAL CHARACTERISTICS**

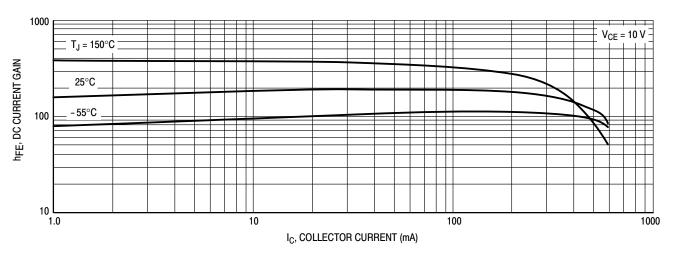


Figure 3. DC Current Gain

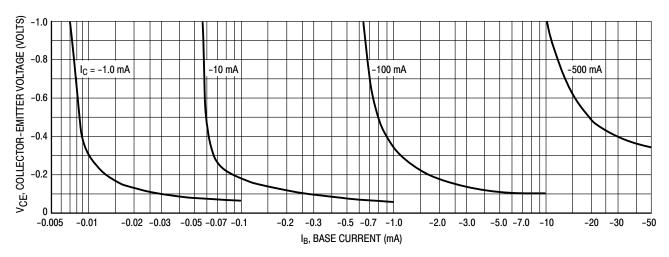


Figure 4. Collector Saturation Region

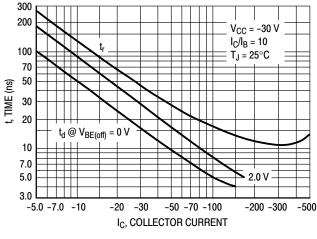


Figure 5. Turn-On Time

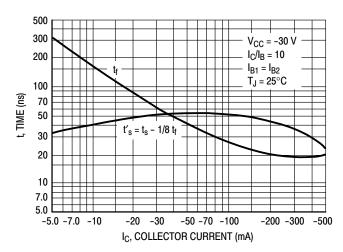
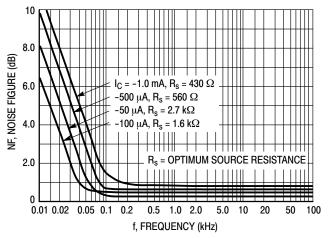


Figure 6. Turn-Off Time

# TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

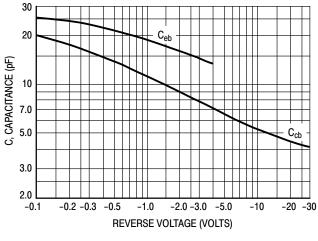
 $V_{CE}$  = 10 Vdc,  $T_A$  = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0  $I_C = -50 \mu A$ -100 μA -500 μA 4.0 -1.0 mA 2.0 100 200 2.0 k 50 k **5**0 1.0 k 5.0 k 10 k 20 k R<sub>s</sub>, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



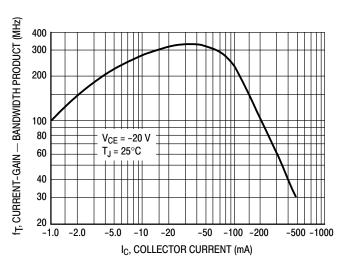
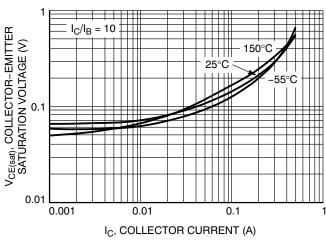


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



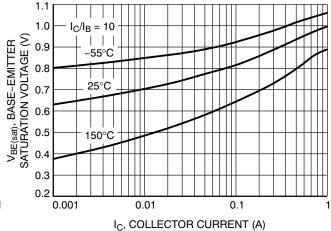
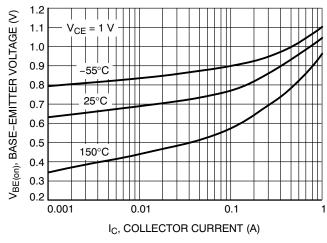


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current

# TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

 $V_{CE}$  = 10 Vdc,  $T_A$  = 25°C



+0.5
0
R<sub>0</sub>VC for V<sub>CE(sat)</sub>
-0.5
-1.0
-2.0
R<sub>0</sub>VB for V<sub>BE</sub>
-2.5
-0.1 -0.2 -0.5 -1.0 -2.0 -5.0 -10 -20 -500
I<sub>C</sub>, COLLECTOR CURRENT (mA)

Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

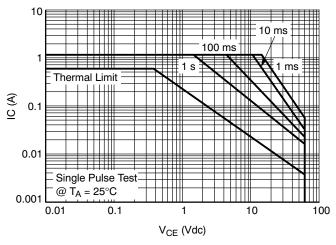
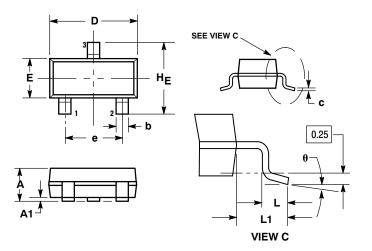


Figure 15. Safe Operating Area

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 



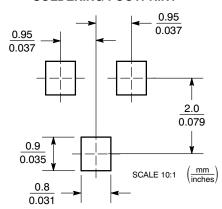
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

PRO	TRUSIONS OR GATE BURRS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
A	O۰		100	N٥		100

STYLE 6: PIN 1. BASE 2 EMITTER COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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